

CLAIMS

1. A method of etching for etching an organic film on a workpiece placed in a hermetically sealed process chamber filled with process gas wherein: the process gas includes at least nitrogen atoms and hydrogen atoms; and
a pressure in the process chamber is substantially higher than 500 mTorr.
 2. A method of etching according to claim 1 wherein the pressure in the process chamber is substantially higher than 500 mTorr.
 3. A method of etching according to claim 1 wherein the nitrogen atoms constitute N_2 and the hydrogen atoms constitute H_2 .
 4. A method of etching according to claim 1 wherein the process gas further includes Ar.
 5. A method of etching according to claim 1 wherein the etching on the organic film is stopped before the etching goes through the organic film.
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